

Holcomb Group Capabilities

**Synchrotron Radiation
& Ultrafast Optics**

West Virginia University



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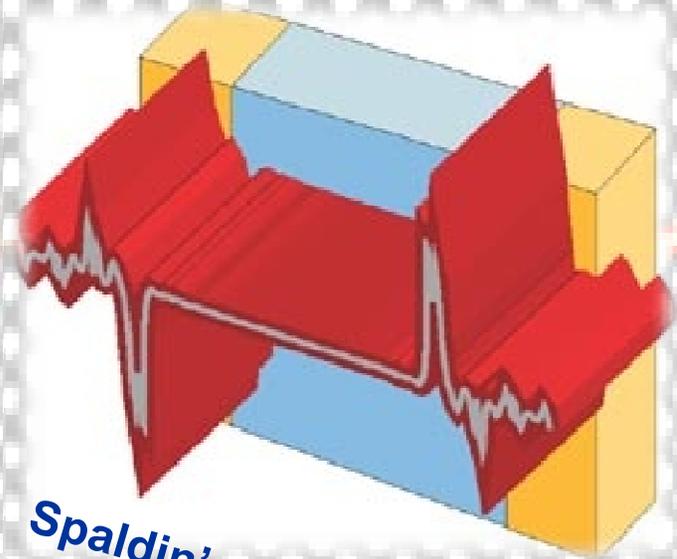
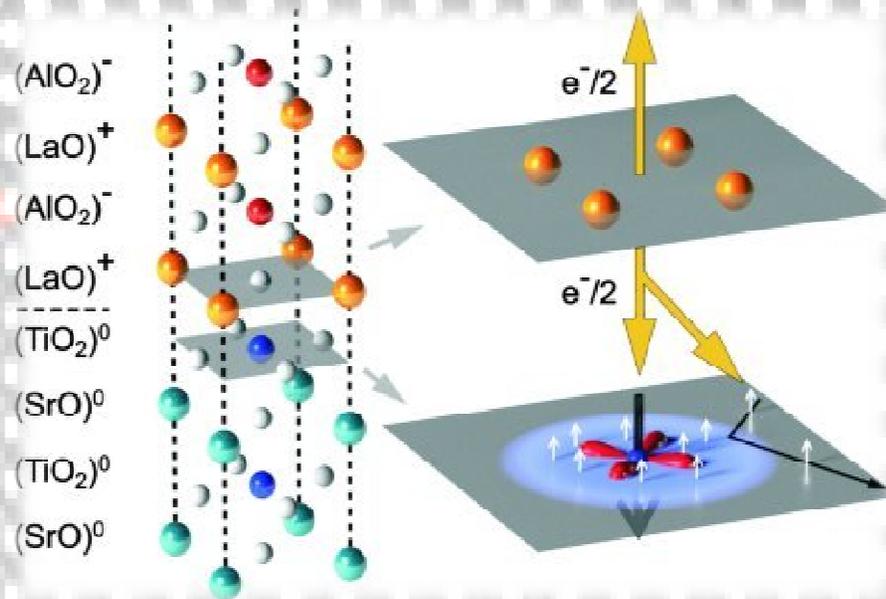


The Physicists' New Playground



“The interface is the device.”

- Herbert Kroemer, beginning of his Nobel Lecture in 2000



Spaldin's spin capacitor

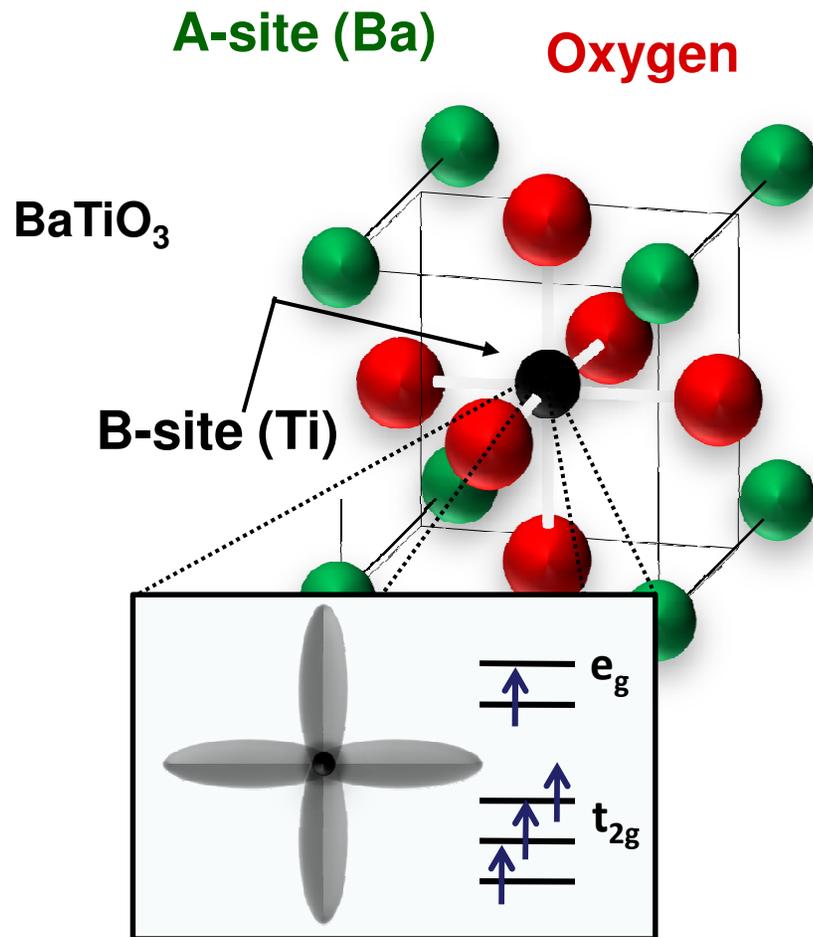


Complex Oxides



Perovskites

- Superconductors ($\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$)
- **Ferroelectrics** (BaTiO_3)
- **Colossal Magnetoresistance** ($(\text{La,Sr})\text{MnO}_3$)
- **Multiferroics** (BiFeO_3)
- High ϵ_r Insulators (SrTiO_3)
- Low ϵ_r Insulators (LaAlO_3)
- Conductors (Sr_2RuO_4)
- Thermoelectrics (doped SrTiO_3)
- Ferromagnets (SrRuO_3)

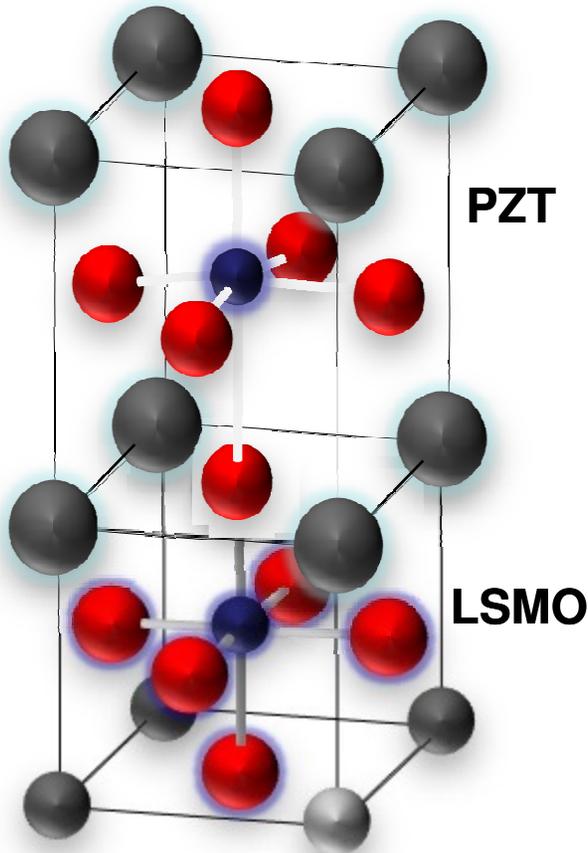


All perovskite-related structures $a, b \sim 3.8\text{-}4.0 \text{ \AA}$

A huge range of oxide crystals : pyrochlores, layered structures, spinels, rock salt, ...



Magnetic & Ferroelectric Heterostructures



- Ferroelectric Perovskites (e.g. PbZrTiO_3)**
- Non-cubic, spontaneous polarization
- “d⁰-ness”
- 6s electrons on A-site

- Magnetic Perovskites (e.g. $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$)**
- Spontaneous magnetization
- Partially filled d-orbitals
- Doping through A-site substitution

Multiferroic Perovskites

- Multiple order parameters
- *Magnetoelectricity* – coupling between electric and magnetic order parameters
- Many pathways to create and influence coupling (strain, thickness, roughness)
- Allow understanding of interfacial physics

Hill (Spaldin), *J. Phys. Chem. B* 104, 6694 (2001)
Kimura, et al., *Nature* 426, 55 (2003)
Hur, ..., Cheong, *Nature* 429, 392 (2004)
Feibig, *J. Phys. D* 38, R123 (2005)
Eerenstein, et al., *Nature* 442, 759 (2006)
Cheong & Mostovoy, *Nature Mater.* 6, 13 (2006)

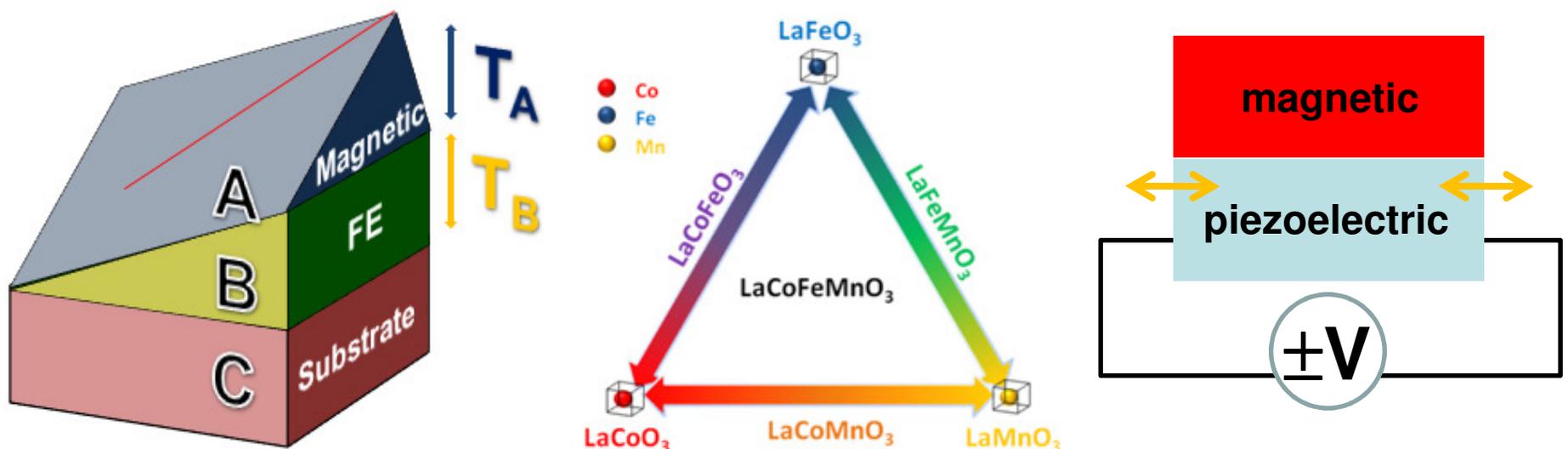


Sample Strategies



The following the heterostructures platforms has been chosen to allow the study of many parameters (including strain and thickness dependence) in the same sample. In this manner we may rule out variations that occur when samples are grown at different times, such as on various substrates. We also compare these results to more standard heterostructures.

Identify the Major Contributor(s) to and Influencers on Interface Coupling.
The effects of thickness, strain and material choice will be investigated by studying wedged, compositionally spread, and piezoelectrically strained (Biegalski, 2010) materials.

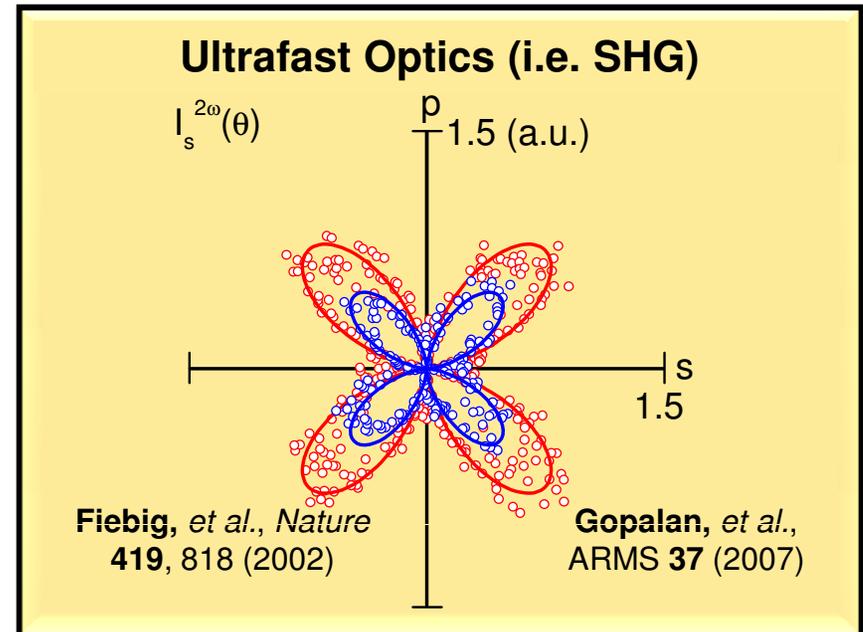
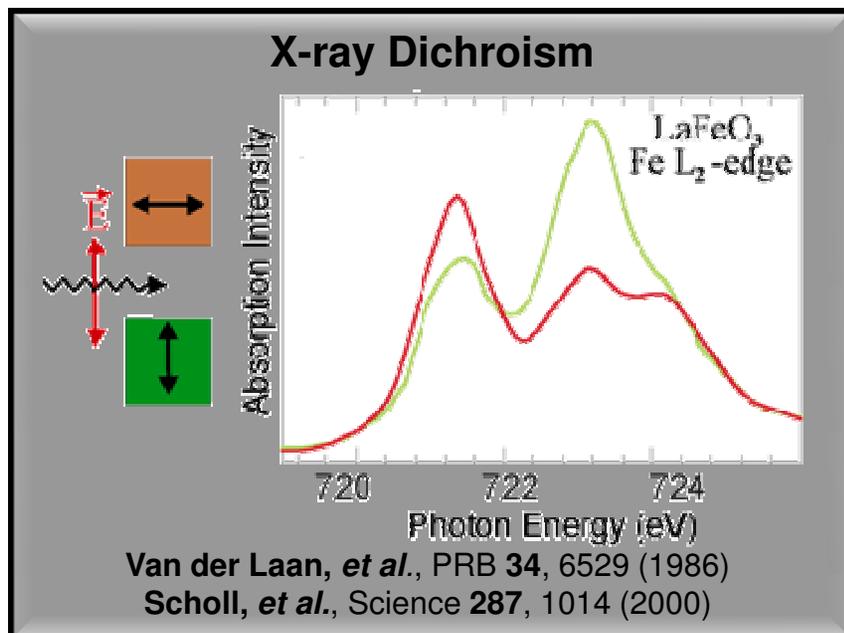




Surface/Interface Characterization



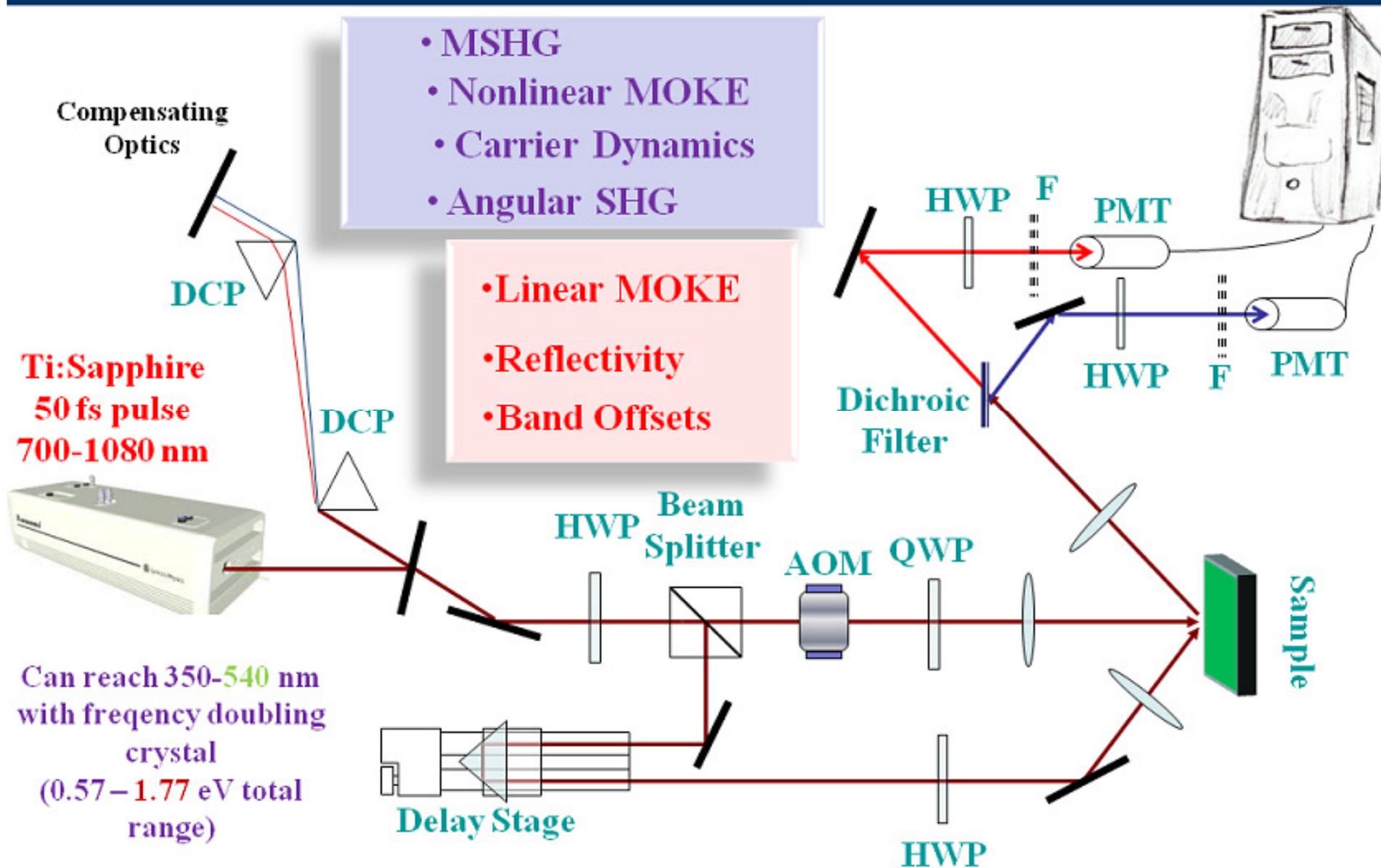
- Imaging domains and determining magnetic and ferroelectric directions in multifunctional materials
- Magnetic dead layers
- Interface imaging



- Carrier dynamics (i.e. rise times and lifetimes)
- Depth-dependent electric and magnetic fields at the surface, interface and bulk
- Symmetry determination
- Band offset measurements



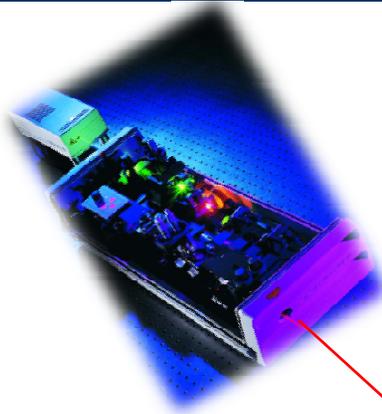
Optical Techniques



In addition to x-ray absorption spectroscopy at national labs

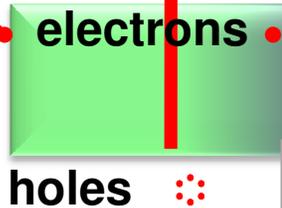


Carrier Dynamics

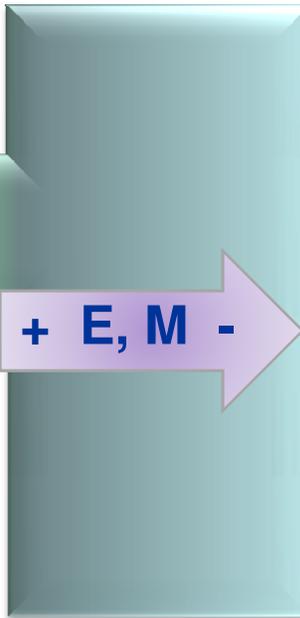


Unlike the Kerr effect, SHG is interface sensitive

Band Gap



Surface



- Contactless, nondestructive technique.
- **Time-dependent SHG** can give information on:
 - Trap Densities and Lifetimes
 - multiphoton electron-hole injection and dynamics.

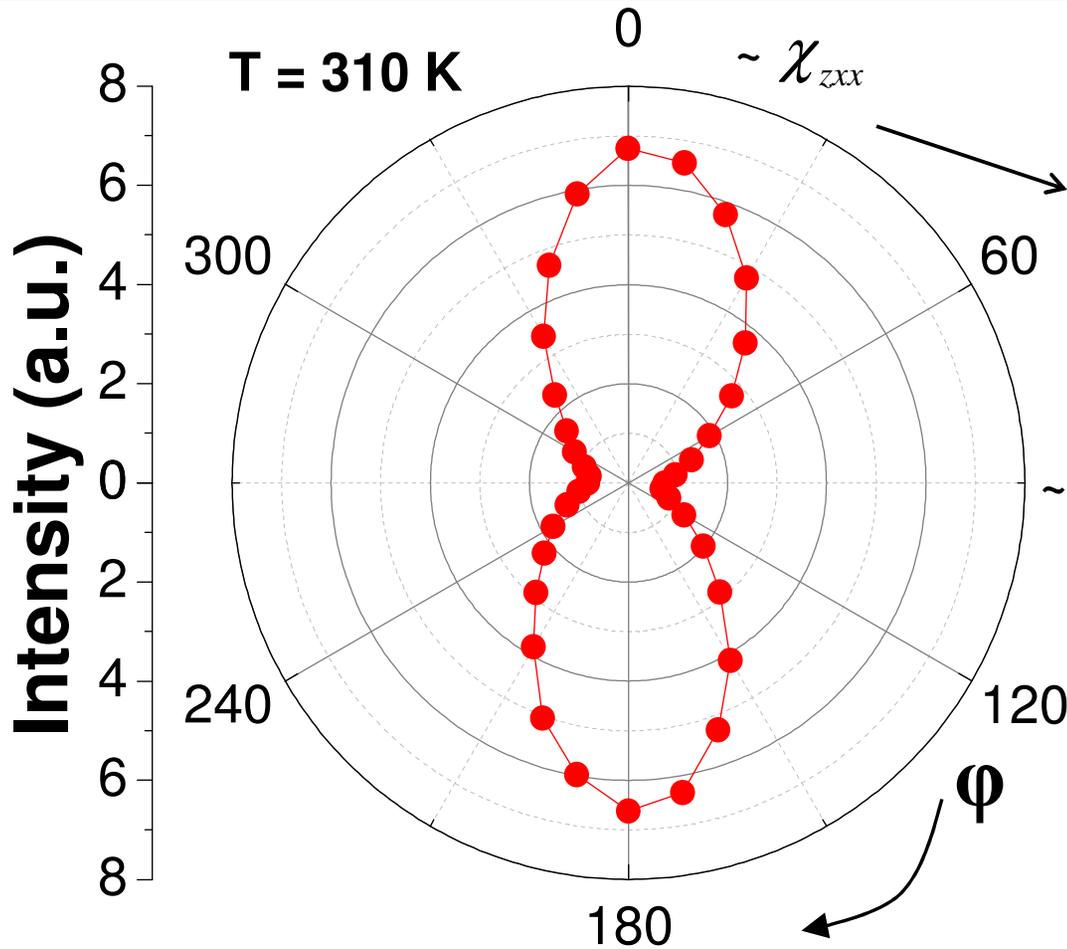
- Excited electrons move to surface
- Separation of electrons and holes creates EM field.

Band Diagram



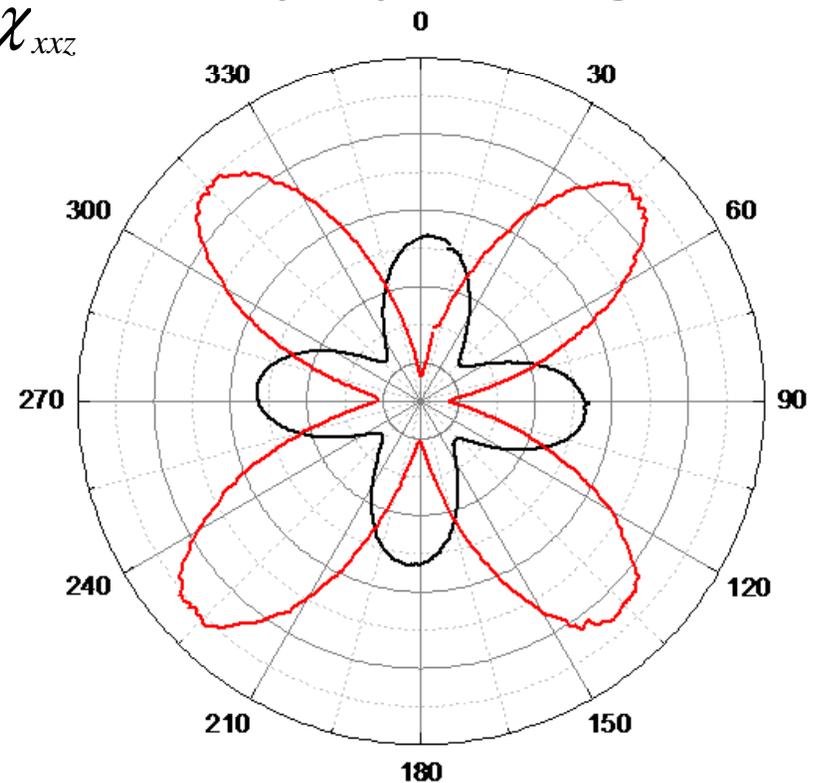


Angular SHG – YMnO₃



$$I_{out}(2\omega) \propto |E_{out}(2\omega)|^2 \propto \cos^6 \phi$$

**One complete rotation of
polarizer/analyzer @ fixed
analyzer/polarizer angle**



**Incident angle $\sim 35^\circ$ with sample
normal; Reflection geometry**

**$\phi=0$ correspond to incident s-polarized
and reflected p-polarized light**



Interfacial Electric & Magnetic Fields



Nonlinear polarization at the frequency 2ω in the presence of quasi-dc interfacial field

$$P_{\pm}^{NL}(2\omega, t) = [\chi^{(2)} + \chi_e^{(3)} \epsilon(t) \pm \chi_m^{(3)} M(t)] [E(\omega)]^2$$

Total Intensity

$$I_{\pm}^{(2\omega)} \propto |P_{\pm}^{NL}|^2$$

Induced SHG intensity

$$\Delta I_{\pm}^{(2\omega)} = I_{\pm}^{(2\omega)} - I_0^{(2\omega)}$$

Extract electric- and magnetic-field-induced contributions

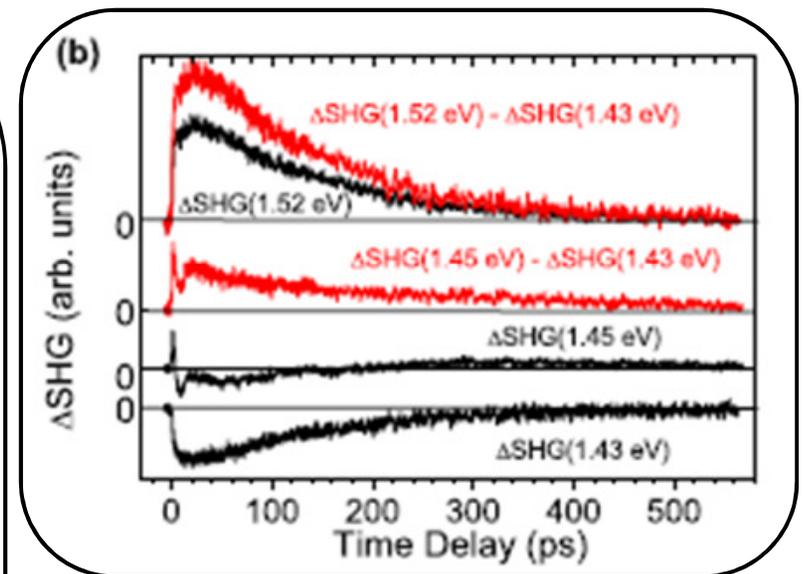
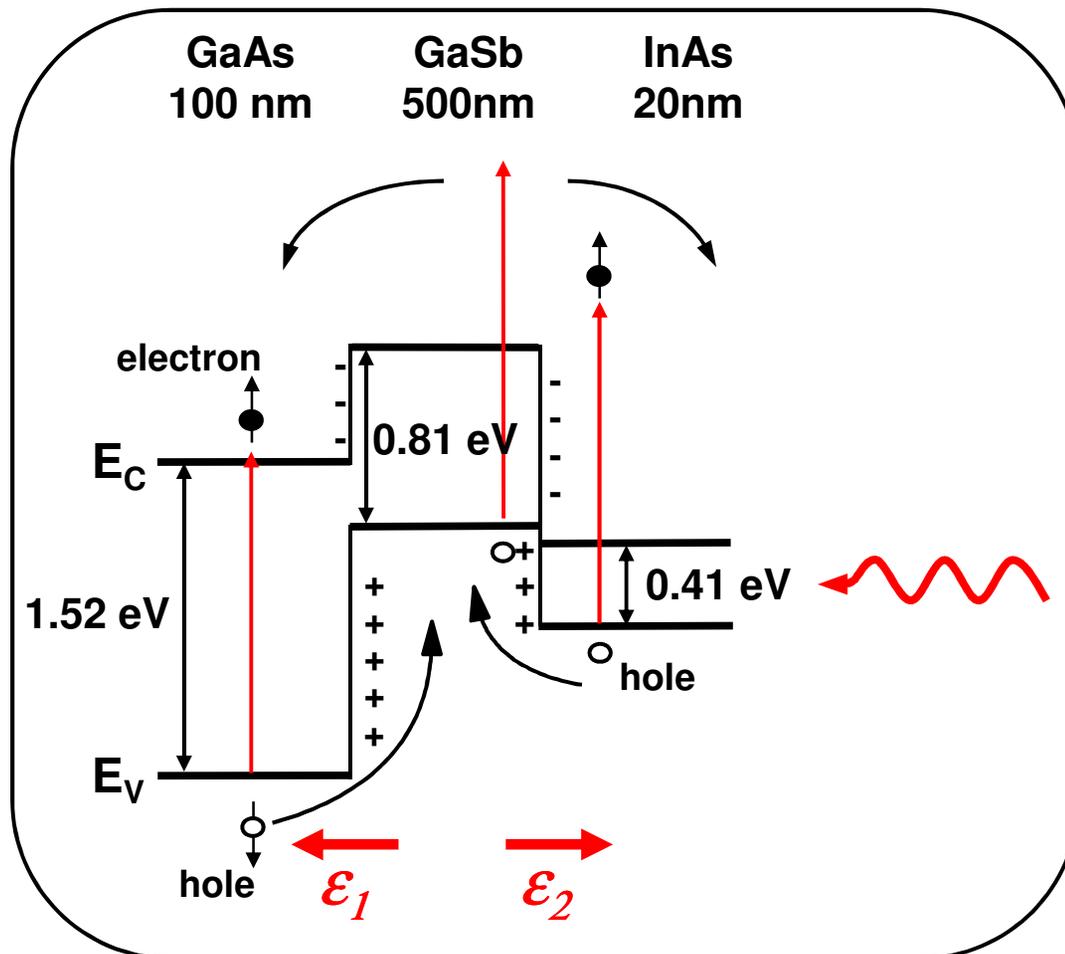
$$\begin{cases} \Delta I_{-}^{(2\omega)} + \Delta I_{+}^{(2\omega)} \propto \epsilon(t) \\ \Delta I_{-}^{(2\omega)} - \Delta I_{+}^{(2\omega)} \propto M(t) \end{cases}$$



Time Dynamics



Time Studies to Reveal the Coupling Dynamics. The excitation of an ensemble of spins by a circularly polarized laser light tuned just above the band gap gives rise to a net magnetization at the interface. By varying the time delay, we obtain valuable information about the dynamics of the carriers across interfaces, such as recombination and spin lifetimes. These times are expected to vary between different compositions and over different thicknesses.



Thermalization/cooling
of electrons and holes

$$\tau_{R1} \sim 2\text{ps}$$

Transport of Spins and Carriers
across Heterostructure

$$\tau_{R2} \sim 15\text{ps}$$

Relaxation of the
Interfacial Magnetic Fields

$$\tau_D \sim 100\text{ps}$$



Dynamic Strain

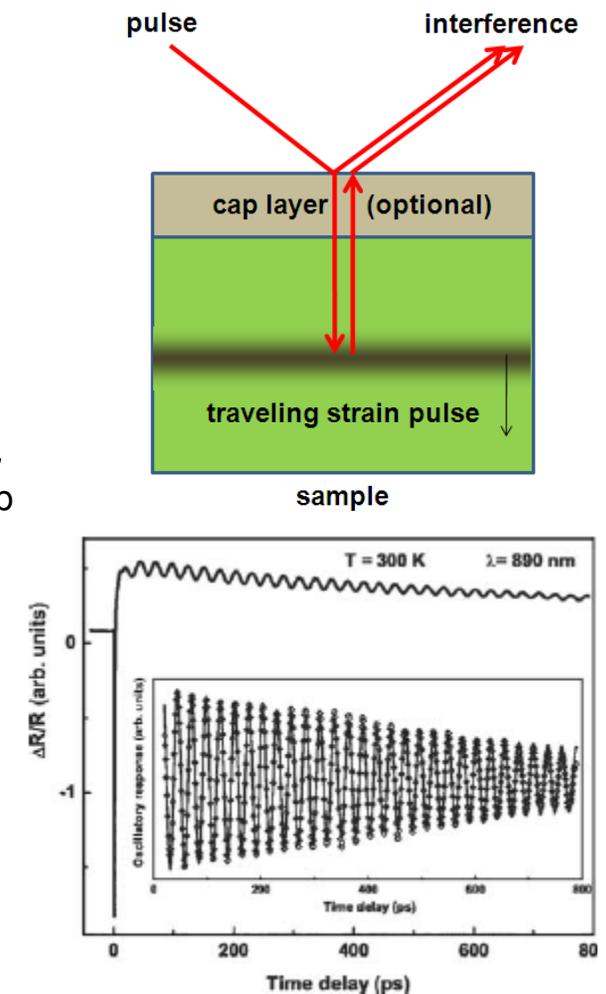


Dynamic Strain Studies to Illuminate Coupling Mechanisms. We should control strain on an ultrashort time scale in order to understand the time dynamics involved. Similar to sound pulses from beating a drum, strain pulses can be generated with intense femtosecond laser pulses.

Reflectivity oscillations originate from the interference of probe beams reflected from the top sample surface and the propagating strain pulse.

$$\Delta R/R \propto A e^{-t/\tau} \cos(2\pi t/T_p + \varphi),$$

where A is the amplitude, τ is the damping time and T_p is the oscillation period. τ is related to the absorption properties of the material by $\tau = 1/(2\alpha V_s) = \lambda/(4\pi V_s \kappa)$, where α is the absorption coefficient and κ is the imaginary part of the complex refractive index $N (=n+i\kappa)$. The amplitude A is connected to the change in the local complex refractive index through the z strain (η_{33}) by the relation $A \propto |\delta N/\delta\eta_{33}|$.



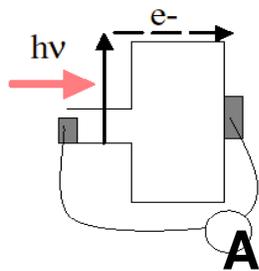


Band Alignment



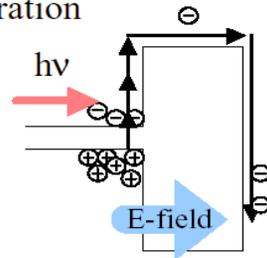
Determine Band Alignment for Promising Magnetoelectric Systems. SHG can also be manipulated to determine band offsets between materials (Jiang *et. al.*, 2003).

Internal PhotoEmission



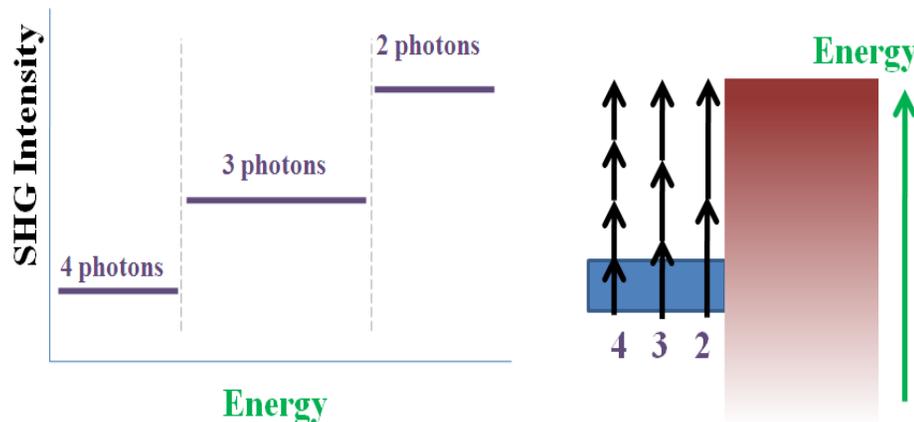
Measure created photocurrent versus wavelength

SHG: Second-Harmonic Generation



Detect Electric-Field Induced Second Harmonic (EFISH) signal at varying wavelengths

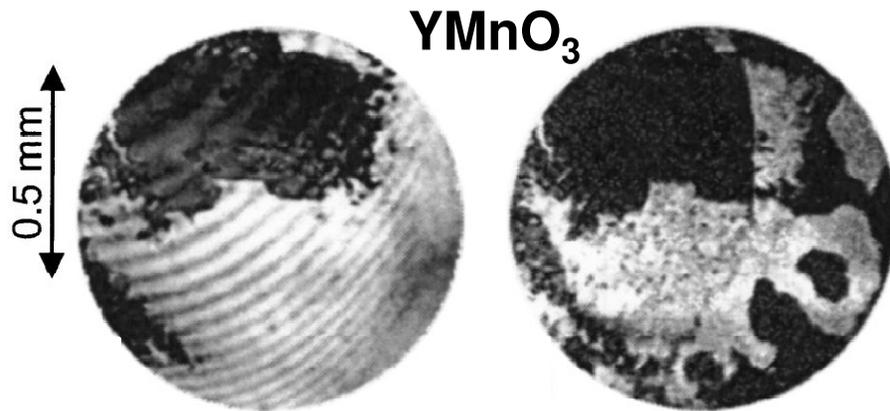
Observation of threshold!



This band alignment can have a strong effect on the interfacial fields and carrier dynamics. Band offsets can be determined by varying the incident light energy and observing a sharp jump in the SHG intensity. This sharp jump occurs when the number of incident photons required to excite an electron to the bottom of the conduction band of the adjoining material changes.



Future Goal: SHG Imaging

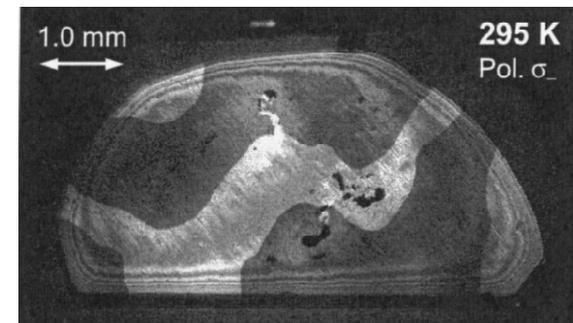


(a) ferroelectric domains and
(b) antiferromagnetic domains

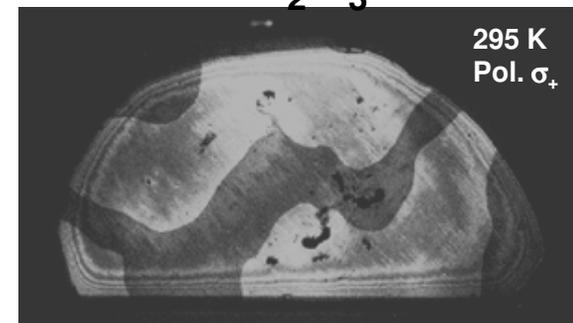
Imaging of both ferroelectric and magnetic domains allows the investigation of multiferroics at various energies

Near field imaging can be purchased for low temperatures and large magnetic fields

Domain imaging using SHG light

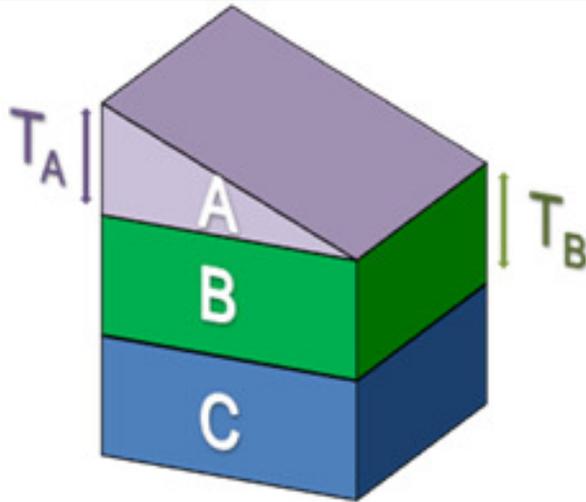


Cr_2O_3

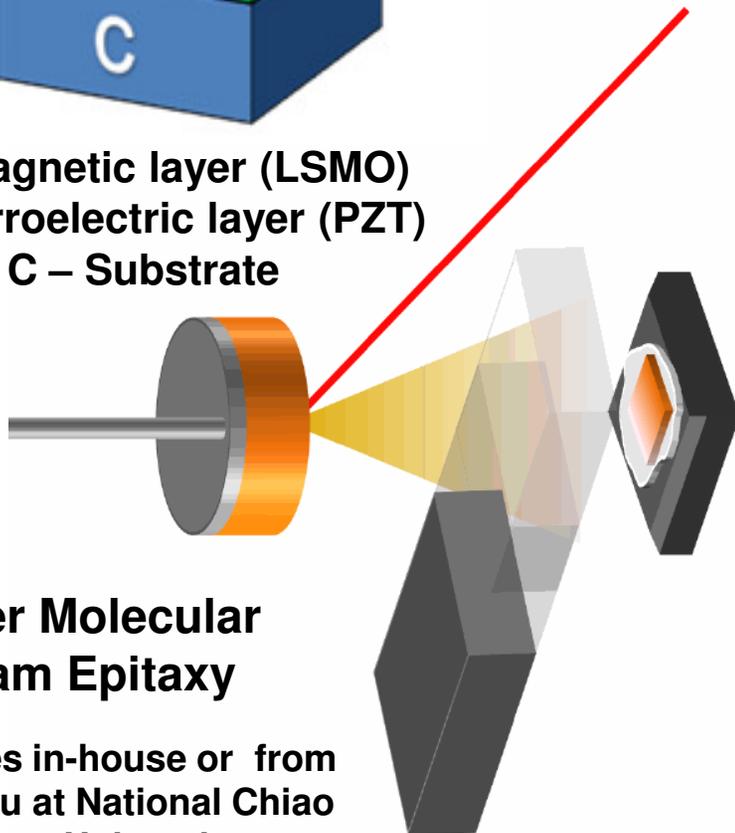


Antiferromagnetic domains

WV Synchrotron Measurements WV

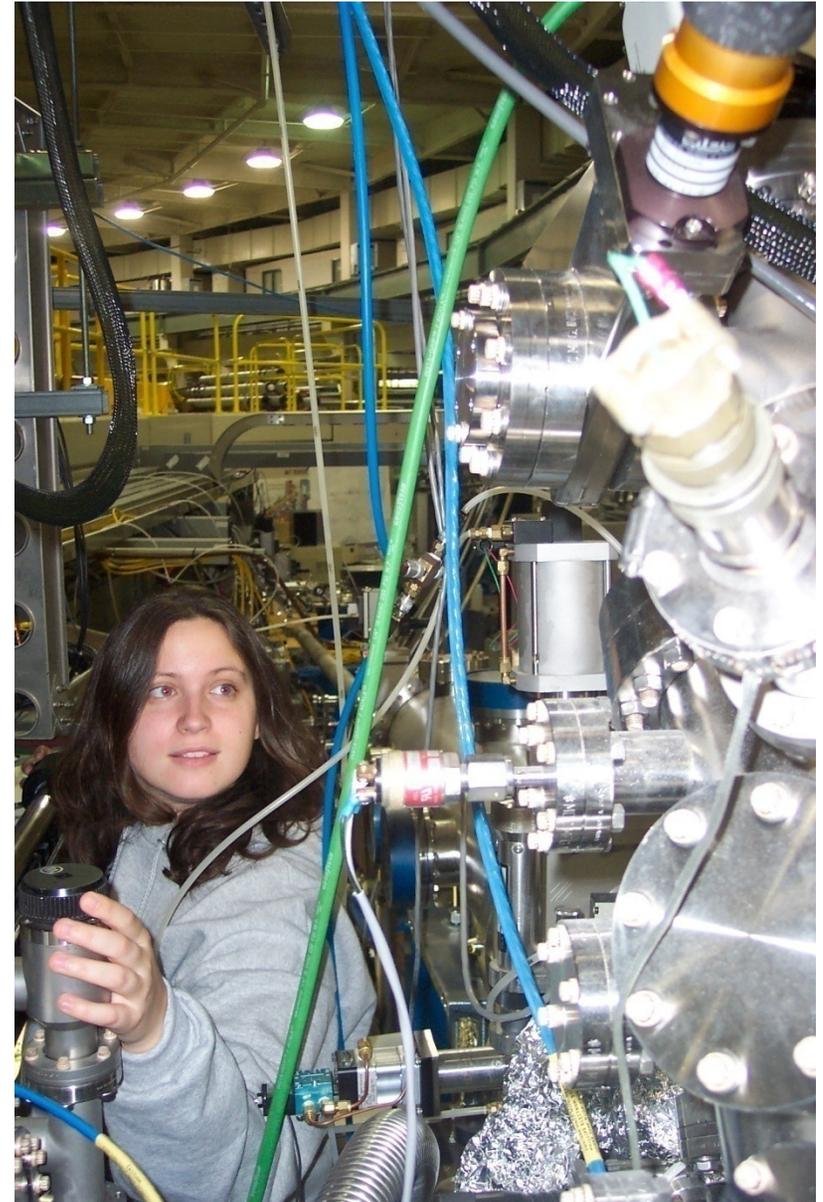


A – Magnetic layer (LSMO)
B – Ferroelectric layer (PZT)
C – Substrate



**Laser Molecular
Beam Epitaxy**

Samples in-house or from
Y.H. Chu at National Chiao
Tung University



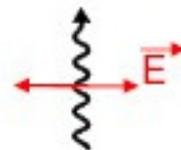
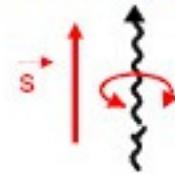
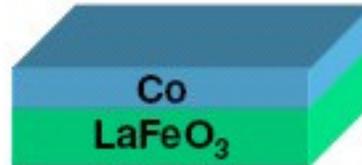
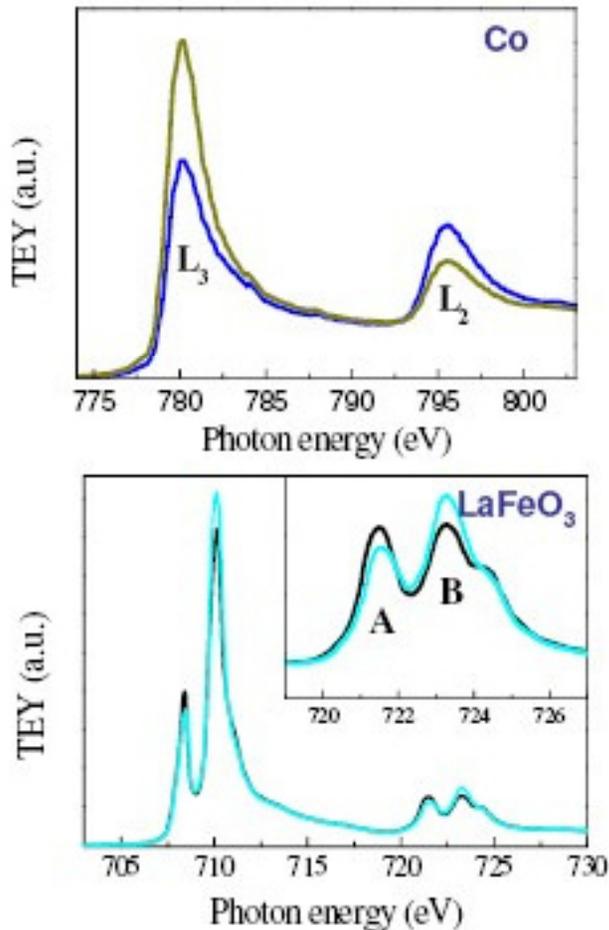


Photoemission Electron Microscopy (PEEM)

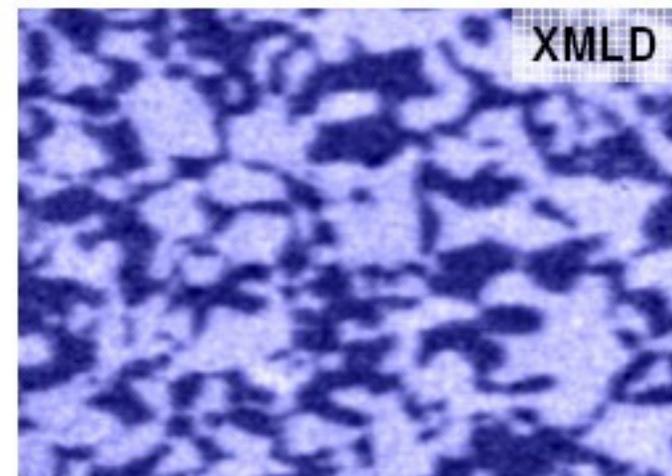
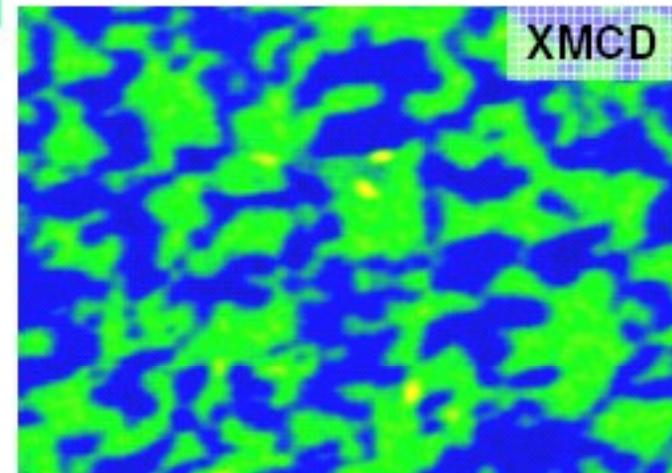


F. Nolting *et al. Nature* 405 (2000)

X-ray Absorption Spectroscopy



Microscopy

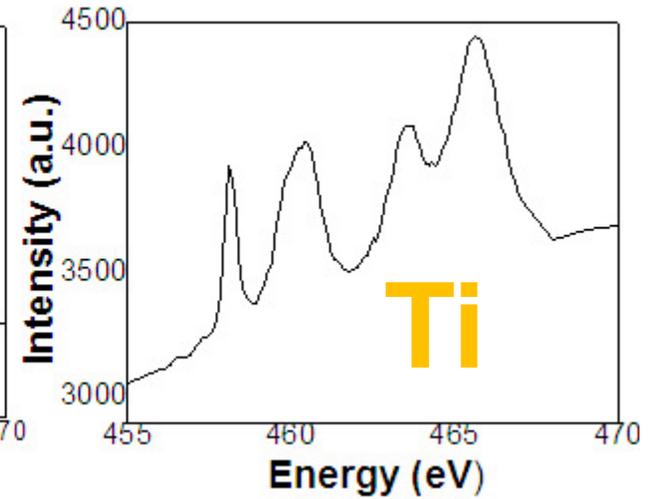
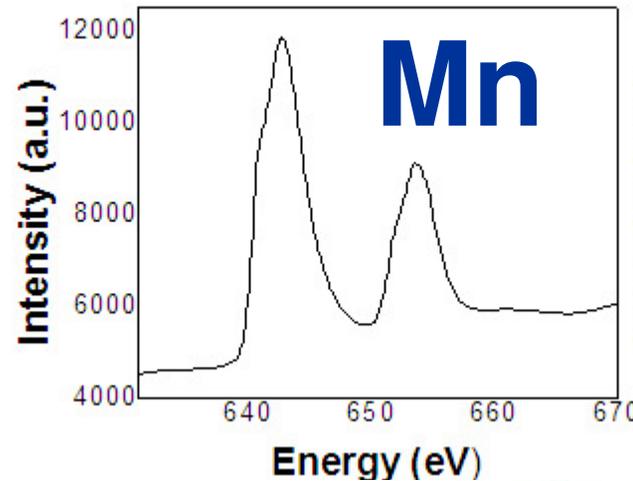
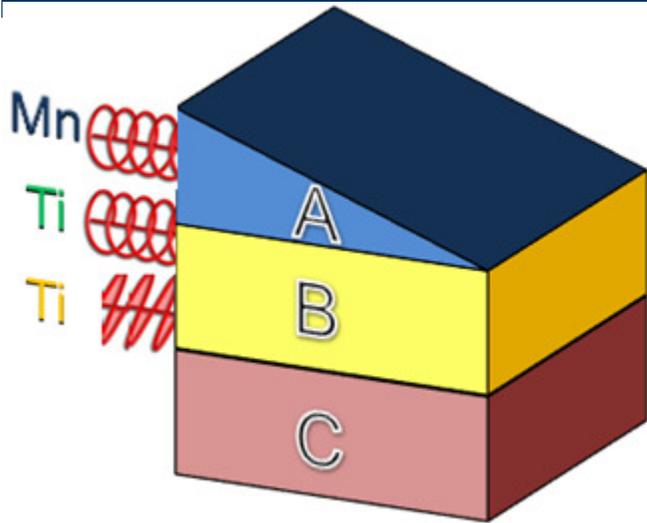


This technique is element specific!

Can we do also see coupling for a magnetic/ferroelectric system?



ME Interface Imaging

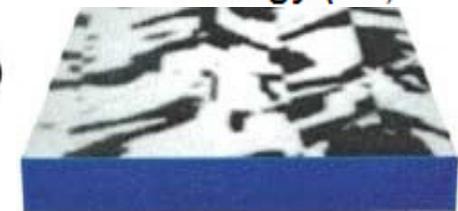


Similar to exchange bias measurements (shown right), we use circularly polarized light on the Ti edge to image any interface magnetism.

Expect interface image to mimic one—if not both—individual layers.



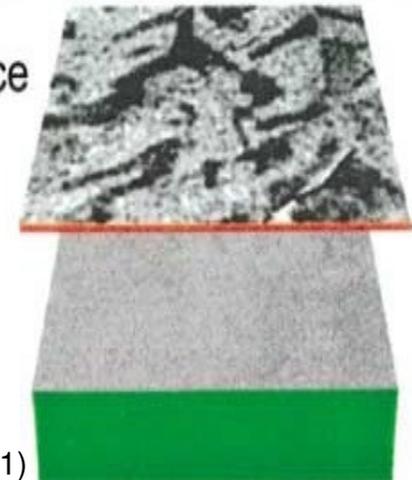
Co



Interface

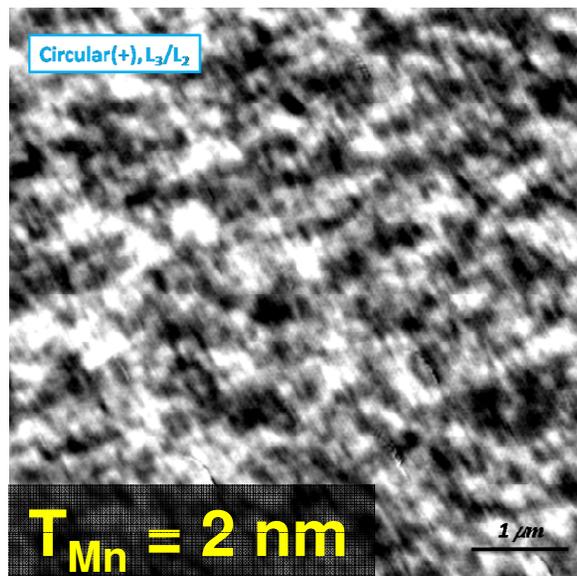


NiO

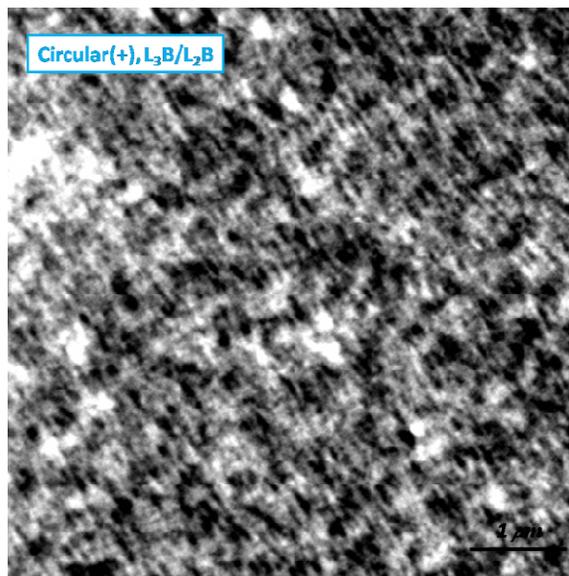




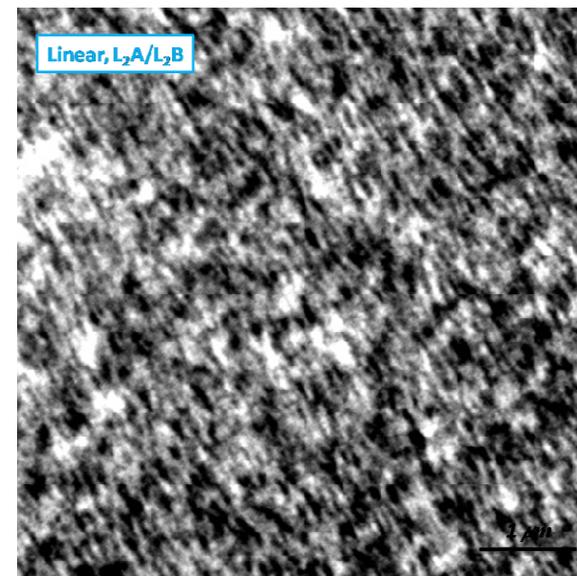
LSMO Thickness Dependence



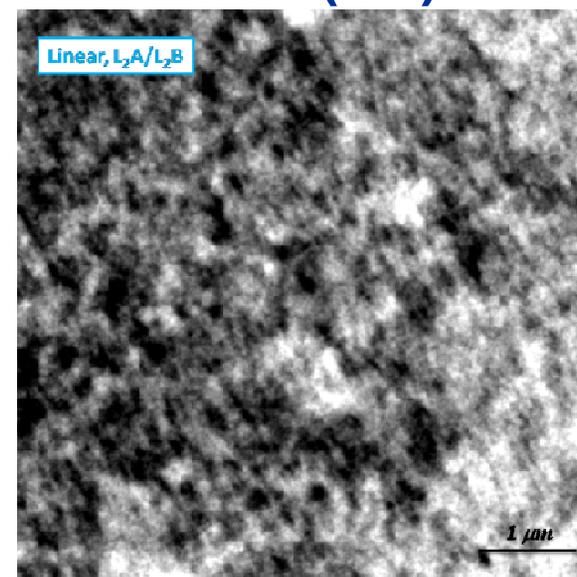
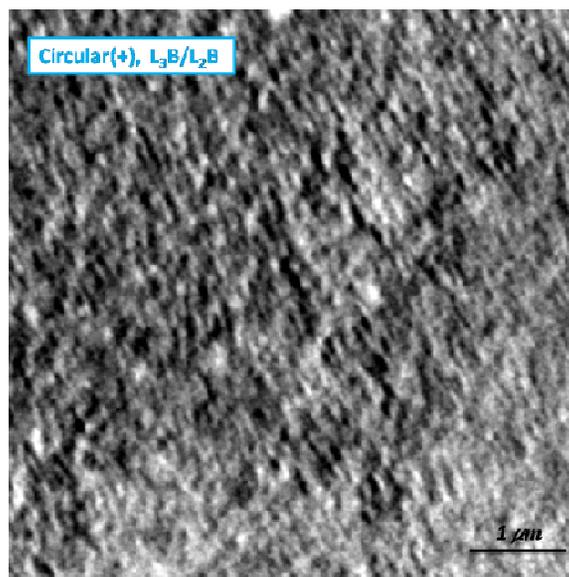
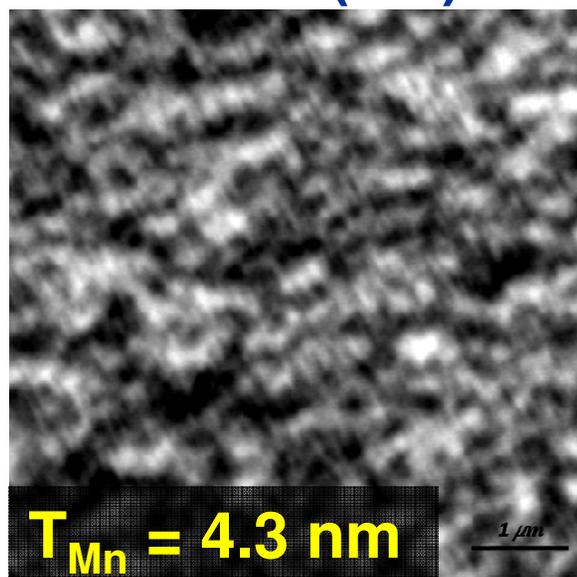
LSMO (FM)



Interface

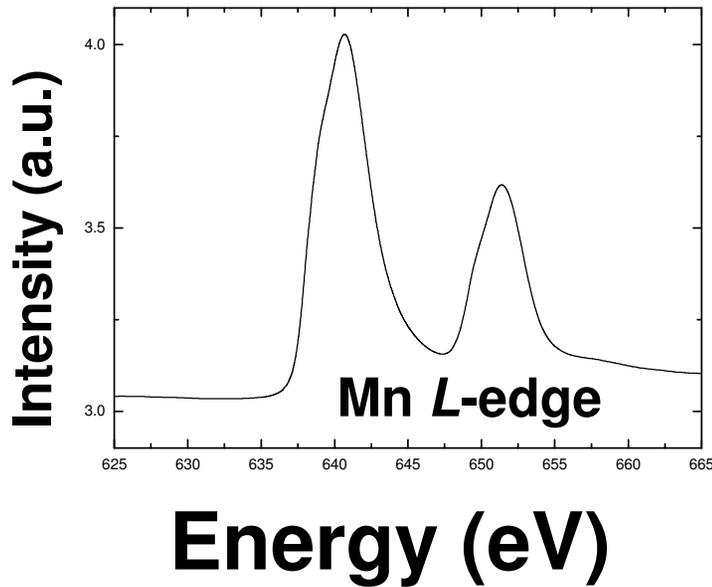


PZT (FE) T=140K



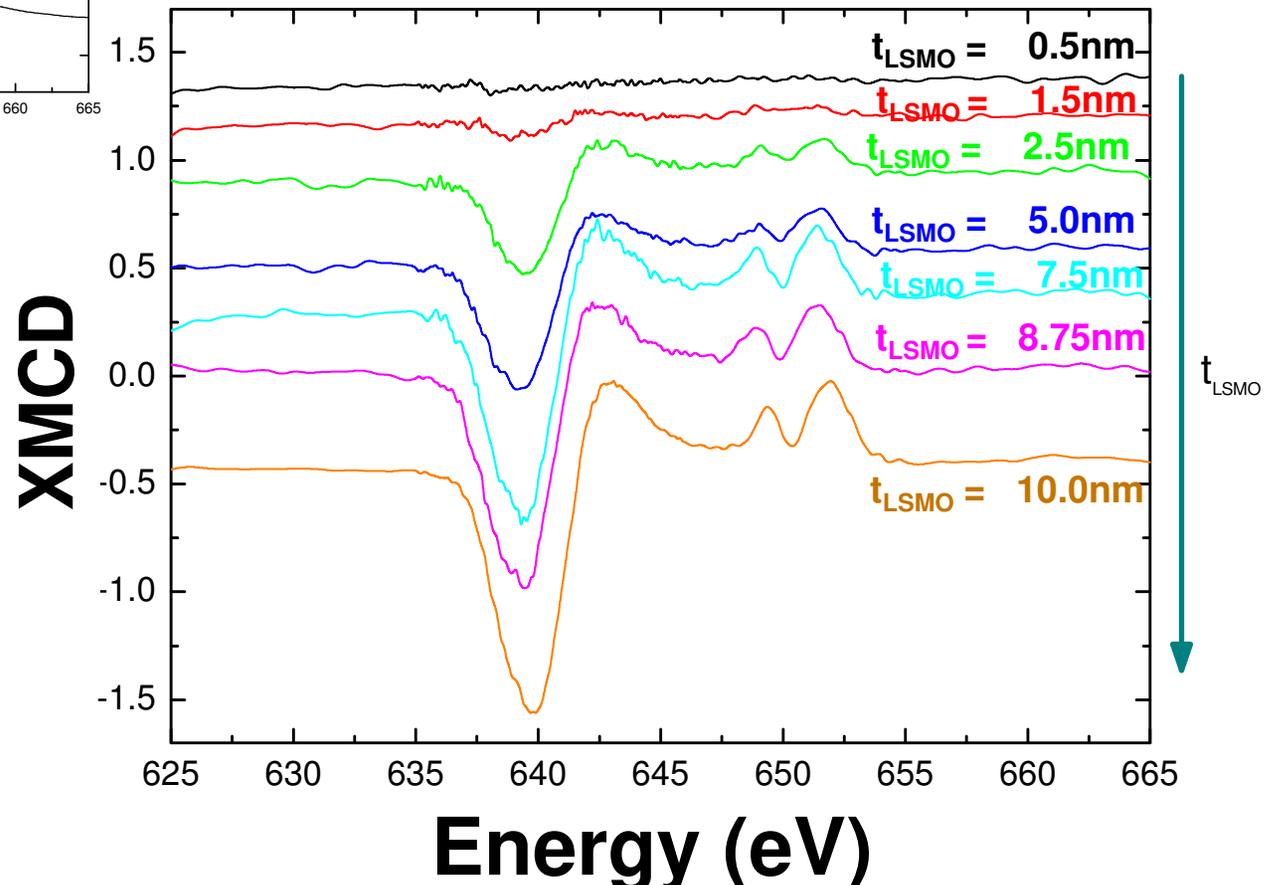


Magnetism of LSMO



Consistent with LSMO magnetic dead layer around 1.2 nm.

Magnetization gradually decreases as the LSMO thickness decreases.

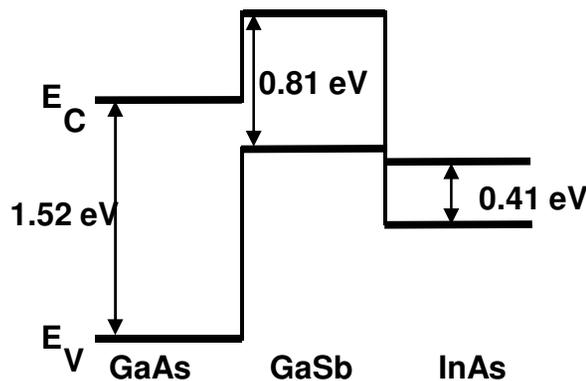




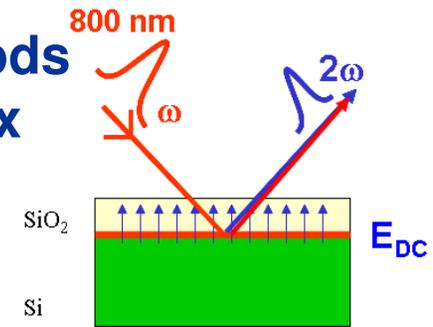
Conclusions



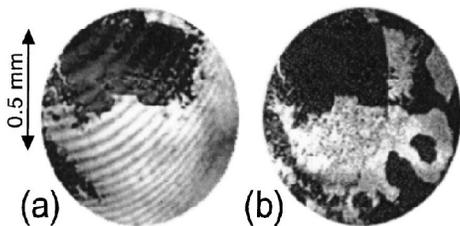
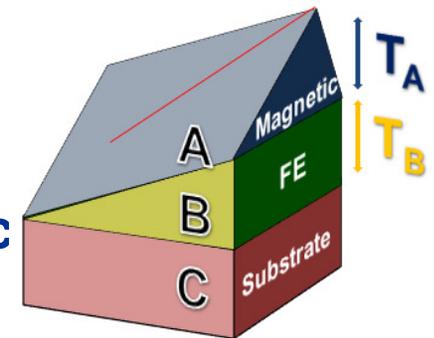
XAS and optics techniques provide many good methods for studying magnets, multiferroics and other complex materials.



Fields, field dynamics, strains, and band offsets can be obtained at interfaces or through depth-dependent studies.



Wedged, compositionally spread or piezoelectrically strained samples of layered ferroelectric and/or magnetic materials allow characterization of interface coupling.



XAS and imaging studies of the heterostructure interfaces can show coupling between the layers and domains.